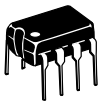
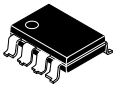
Green Mode Buck Switch

FSL306LR



PDIP−7 (PDIP−8 LESS PIN 6)
CASE 626A



PDIP7 MINUS PIN 6 GW
CASE 707AA

Description

The FSL306LR integrate Pulse Width Modulator (PWM) and SENSEFET® is specifically designed for high−performance offline buck, buck−boost, and non−isolation flyback Switched Mode Power Supplies (SMPS) with minimal external components. This device integrates a high−voltage power regulator that enables operation without auxiliary bias winding. An internal transconductance amplifier reduces external components for the feedback compensation circuit.

The integrated PWM controller includes: 10 V regulator for no external bias circuit, Under−Voltage Lockout (UVLO), Leading−Edge Blanking (LEB), an optimized gate turn−on / turn−off driver, EMI attenuator, Thermal Shutdown (TSD), temperature−compensated precision current sources for loop compensation, and fault−protection circuitry. Protections include: Overload Protection (OLP), Over−Voltage Protection (OVP), Feedback Open Loop Protection (FB_OLP), and Abnormal Over−Current Protection (AOCP). FSL306LR offers good soft−start performance during startup.

The internal high−voltage startup switch and the Burst−Mode operation with very low operating current reduce the power loss in Standby Mode. As the result, it is possible to reach power loss of 120 mW without external bias and 25 mW with external bias when input voltage is 230 V_{AC}.

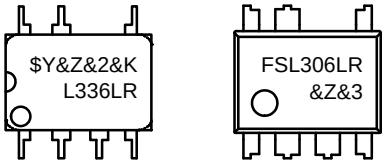
Features

- Built−in Avalanche Rugged SENSEFET: 650 V
- Fixed Operating Frequency: 50 kHz
- No−Load Power Consumption:
  <25 mW at 230 V_{AC} with External Bias;
  <120 mW at 230 V_{AC} without External Bias
- No Need for Auxiliary Bias Winding
- Frequency Modulation for Attenuating EMI
- Pulse−by−Pulse Current Limiting
- Ultra−Low Operating Current: 250 μA
- Built−in Soft−Start and Startup Circuit
- Adjustable Peak Current Limit
- Built−in Transconductance (Error) Amplifier
- Various Protections: Overload Protection (OLP), Over−Voltage Protection (OVP), Feedback Open Loop Protection (FB_OLP), AOCP (Abnormal Over−Current Protection), Thermal Shutdown (TSD)
- Fixed 650 ms Restart Time for Safe Auto−Restart Mode of All Protections
- These Devices are Pb−Free, Halide Free and are RoHS Compliant

Applications

- SMPS for Home Appliances and Industrial Applications
- SMPS for Auxiliary Power

MARKING DIAGRAM



FSL306LRN FSL306LRLX

LR306LR = Specific Device Code
FSR306LR
Y = Logo
&Z = Assembly Plant Code
&2 = 2−Digit Date Code
&3 = 3−Digit Date Code
&K = 2−Digits Lot Run Traceability Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 13 of this data sheet.

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APPLICATION DIAGRAMS

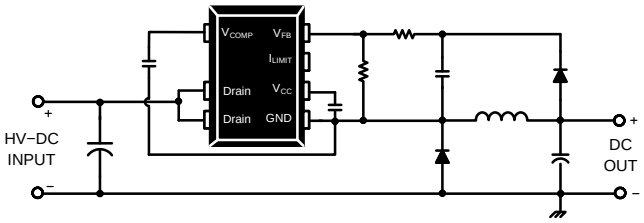

Figure 1. Buck Converter Application

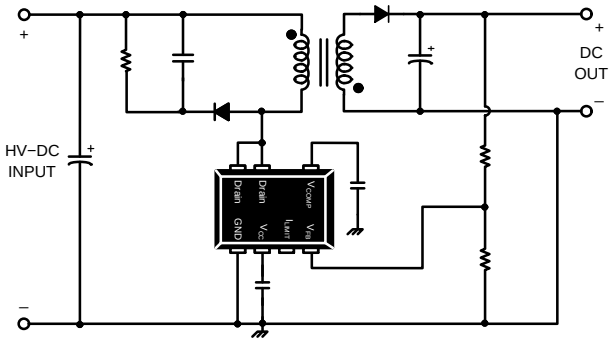

Figure 2. Non−Isolation Flyback Converter Application

BLOCK DIAGRAM

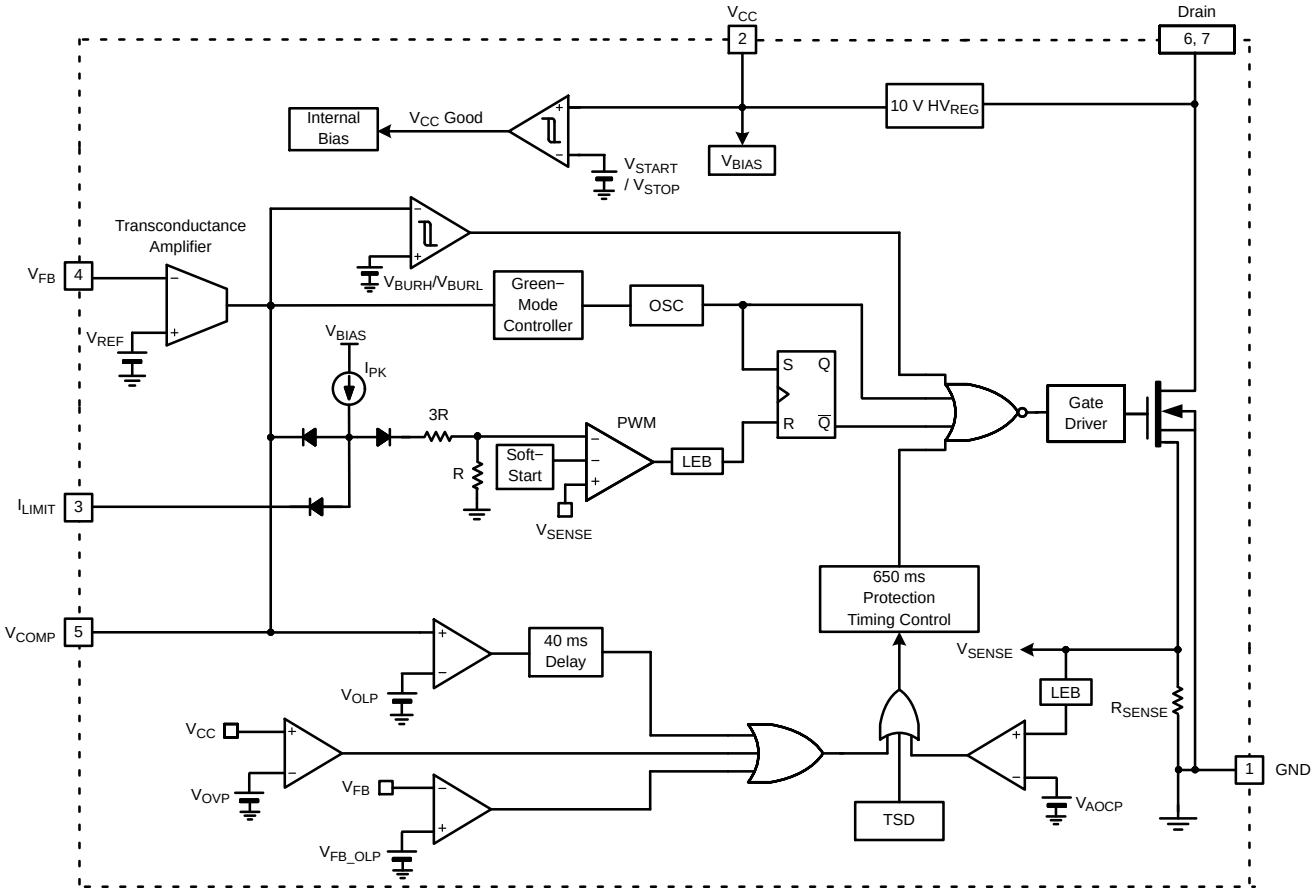

Figure 3. Internal Block Diagram

PIN CONFIGURATION

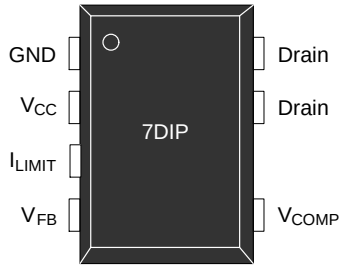

Figure 4. Pin Configuration

PIN DEFINITIONS

Pin #	Name	Description
1	GND	*Ground*. SENSEFET source terminal on the primary side and internal control ground.
2	V_{CC}	*Positive Supply Voltage Input*. This pin is the positive supply input, which provides the internal operating current for startup and steady−state operation. This pin voltage is regulated to 10 V, without the external bias circuit, via an internal 10−V HVREG switch *(see Figure 3)*. When the external bias voltage is higher then10 V, it disables the internal high−voltage regulator to reduces power consumption.
3	I_{LIMIT}	*Peak Current Limit*. Adjusts the peak current limit of the SENSEFET. The internal 50 μA current source is diverted to the parallel combination of an internal 46 kΩ (3R + R) resistors and any external resistor to GND on this pin to determine the peak current limit.
4	V_{FB}	*Feedback Voltage*. Inverting input of the transconductance amplifier. This pin controls converter output voltage by outputting a VCOMP−pin current proportional to the difference between the reference voltage and the output voltage divided by external resistor divider.
5	V_{COMP}	*Comp Voltage*. Output of the transconductance amplifier. The compensation networks are placed between the V_{COMP} and GND pins to achieve stability and good dynamic performance.
6, 7	Drain	*Drain*. High−voltage power SENSEFET drain connection. In addition, during startup and steady−state operation; the internal high−voltage current source supplies internal bias and charges the external capacitor connected to the V_{CC} pin. Once V_{CC} reaches 8 V, all internal blocks are activated. The internal high−voltage current source is enabled until V_{CC} reaches 10 V. After that, the internal high−voltage regulator turns on and off regularly to maintain V_{CC} at 10 V.

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C unless otherwise specified)

Symbol	Parameter	Min	Max	Unit
V_{DS}	Drain Pin Voltage	−0.3	650.0	V
V_{CC}	Supply Voltage	−0.3	26.0	V
V_{COMP}	V_{COMP} Pin Voltage	−0.3	Internally Clamped Voltage (Note 1)	V
V_{FB}	Feedback Voltage	−0.3	12.0	V
I_{LIMIT}	Current Limit Pin Voltage	−0.3	12.0	V
I_{DM}	Drain Current Pulsed (Note 2)	−	2.8	A
E_{AS}	Single Pulsed Avalanche Energy (Note 3)	−	10.5	mJ
P_D	Total Power Dissipation	−	1.25	W
T_J	Operating Junction Temperature (Note 4)	−40	125	°C
	Maximum Junction Temperature	−	150	°C
T_{STG}	Storage Temperature	−55	150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. V_{COMP} is clamped by internal clamping diode (11 V, I_{CLAMP_MAX} < 100 μA).
2. Repetitive rating: pulse width is limited by maximum junction temperature.
3. L = 10 mH, starting T_J = 25°C.
4. Although this parameter guarantees IC operation, it does not guarantee all electrical characteristics.

THERMAL IMPEDANCE (T_A = 25°C unless otherwise specified)

Symbol	Characteristic	Value	Unit
θ_{JA}	Junction−to−Ambient Thermal Impedance (Note 5)	100	°C/W

5. JEDEC recommended environment, JESD51−2, and test board, JESD51−3, with minimum land pattern.

ESD CAPABILITY

Symbol	Characteristic	Value	Unit
ESD	Human Body Model, JESD22−A114 (Note 6)	4	kV
	Charged Device Model, JESD22−C101 (Note 6)	2	

6. Meets JEDEC standards JESD22−A114 and JESD 22−C101.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise specified)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
SENSEFET SECTION						
BV_{DSS}	Drain Source Breakdown Voltage	V_{CC} = 0 V, I_D = 250 μA	650	−	−	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 520 V, T_A = 125°C	−	−	250	μA
$R_{DS(ON)}$	Drain−Source On−State Resistance	V_{GS} = 10 V, I_D = 0.3 A	−	12	18	Ω
C_{ISS}	Input Capacitances	V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz	−	97	−	pF
C_{OSS}	Output Capacitance	V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz	−	13.6	−	pF
C_{RSS}	Reverse Transfer Capacitance	V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz	−	2.4	−	pF
t_r	Rise Time	V_{DD} = 325 V, I_D = 0.7 A	−	7.6	−	ns
t_f	Fall Time	V_{DD} = 325 V, I_D = 0.7 A	−	26.1	−	ns

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise specified) (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
CONTROL SECTION						
f_{OSC}	Switching Frequency	V_{COMP} = 2.5 V	45	50	55	kHz
f_M	Frequency Modulation (Note 7)	V_{COMP} = 2.5 V, Randomly	−	±3	−	kHz
$t_{on.max}$	Maximum Turn−On Time	V_{COMP} = 2.5 V	11.2	13.3	15.4	μs
V_{START}	UVLO Threshold Voltage	V_{COMP} = 0 V, V_{CC} Sweep	7.2	8.0	8.8	V
V_{STOP}		After Turn On	6.3	7.0	7.7	V
I_{PK}	Current Limit Source Current	V_{COMP} = 2.5 V	35	50	65	μA
t_{SS}	Soft−Start Time	V_{COMP} = 2.5 V	7	10	13	ms
BURST MODE SECTION						
V_{BURH}	Burst−mode HIGH Threshold Voltage	V_{CC} = 15 V, V_{COMP} Increase	0.58	0.65	0.72	V
V_{BURL}	Burst−mode LOW Threshold Voltage	V_{CC} = 15 V, V_{COMP} Decrease	0.52	0.59	0.66	V
HYS_{BUR}	Burst−mode Hysteresis		−	60	−	mV
PROTECTION SECTION						
I_{LIM}	Peak Current Limit	V_{COMP} = 2.5 V, di/dt = 300 mA/μs	0.40	0.45	0.50	A
t_{CLD}	Current Limit Delay (Note 7)		−	−	200	ns
V_{OLP}	Overload Protection	V_{COMP} Increase	2.7	3.0	3.3	V
V_{AOCP}	Abnormal Over−Current Protection (Note 7)	V_{COMP} = 2.5 V	0.8	1.0	1.2	V
t_{LEB}	Leading−Edge Blanking Time (Note 7)		−	200	−	ns
V_{FB_OLP}	FB Open Loop Protection	V_{FB} Decrease	0.4	0.5	0.6	V
V_{OVP}	Over−Voltage Protection	V_{CC} Increase	23.0	24.5	26.0	V
TSD	Thermal Shutdown Temperature (Note 7)		125	135	150	°C
HYS_{TSD}	TSD Hysteresis Temperature (Note 7)		−	60	−	°C
t_{DELAY}	Over Load Protection Delay (Note 7)	V_{COMP} > 3 V	−	40	−	ms
$t_{RESTART}$	Restart Time After Protection (Note 7)		−	650	−	ms
TRANSCONDUCTANCE AMPLIFIER SECTION						
G_m	Transconductance of Error Amplifier		190	240	290	μmho
V_{REF}	Voltage Feedback Reference		2.45	2.50	2.55	V
$I_{EA.SR}$	Output Sourcing Current	V_{FB} = V_{REF} − 0.05 V	−	−12	−	μA
$I_{EA.SK}$	Output Sink Current	V_{FB} = V_{REF} + 0.05 V	−	12	−	μA
HIGH−VOLTAGE REGULATOR SECTION						
V_{HVREG}	HV Regulator Voltage	V_{COMP} = 0 V, V_{DRAIN} = 40 V	9	10	11	V
TOTAL DEVICE SECTION						
I_{OP1}	Operating Supply Current (Control Part Only, without Switching)	0 V < V_{COMP} < V_{BURL}	−	0.25	0.35	mA
I_{OP2}	Operating Supply Current (While Switching)	V_{BURL} < V_{COMP} < V_{OLP}	−	0.8	1.3	mA
I_{CH}	Startup Charging Current	V_{CC} = 0 V, V_{DRAIN} > 40 V	−	6	−	mA
I_{START}	Startup Current	V_{CC} = Before V_{START}, V_{COMP} = 0 V	−	120	155	μA
V_{DRAIN}	Minimum Drain Supply Voltage	V_{CC} = V_{COMP} = 0 V, V_{DRAIN} Increase	−	35	−	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

7. Though guaranteed by design, they are not 100% tested in production.

TYPICAL PERFORMANCE CHARACTERISTICS

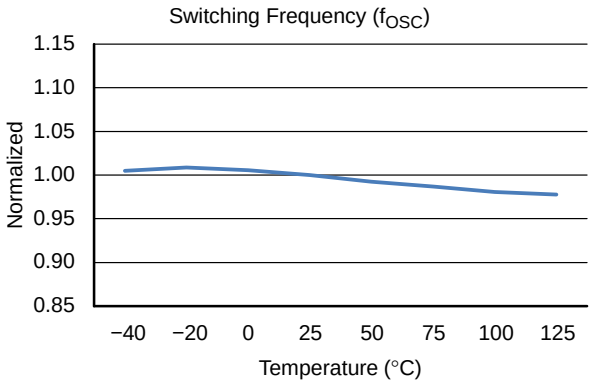

Figure 5. Operating Frequency vs. Temperature

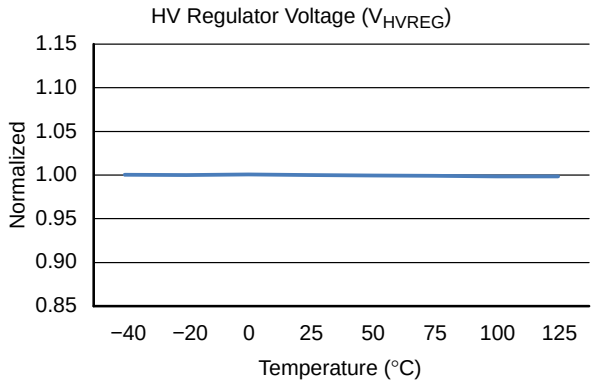

Figure 6. HV Regulator Voltage vs. Temperature

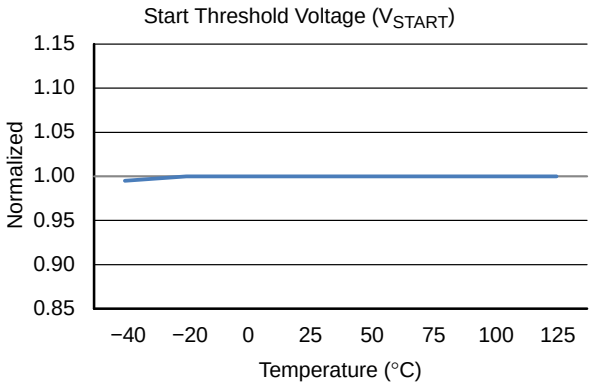

Figure 7. Start Threshold Voltage vs. Temperature

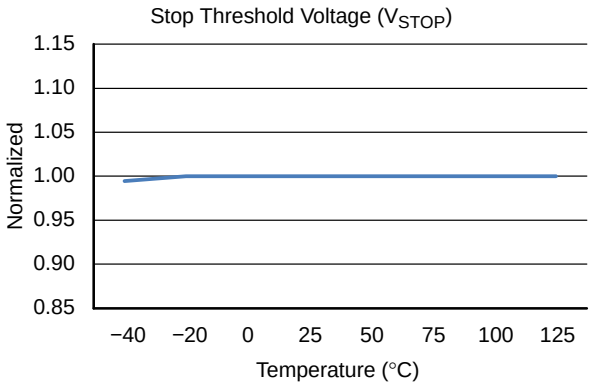

Figure 8. Stop Threshold Voltage vs. Temperature

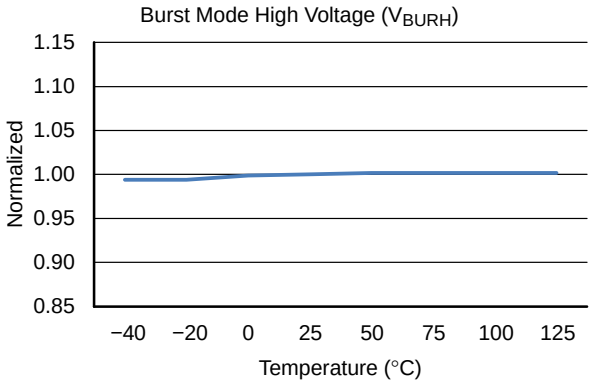

Figure 9. Burst Mode High Voltage vs. Temperature

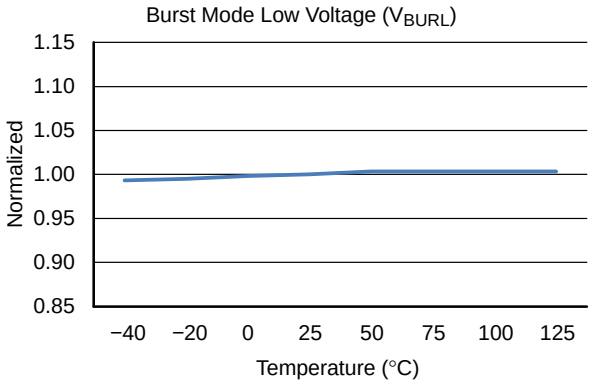

Figure 10. Burst Mode Low Voltage vs. Temperature

TYPICAL PERFORMANCE CHARACTERISTICS (continued)

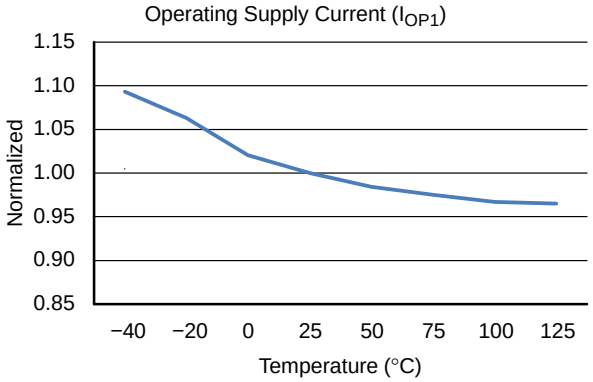

Figure 11. Operating Supply Current 1 vs. Temperature

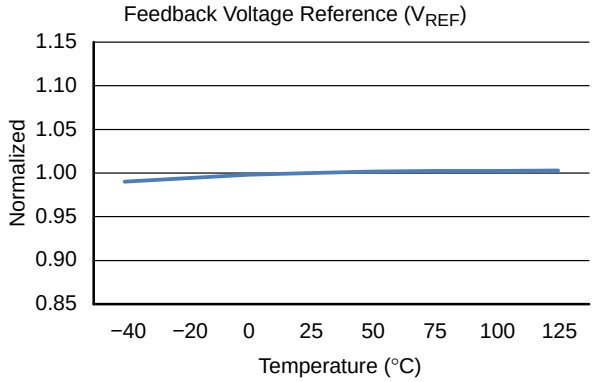

Figure 12. Feedback Voltage Reference vs. Temperature

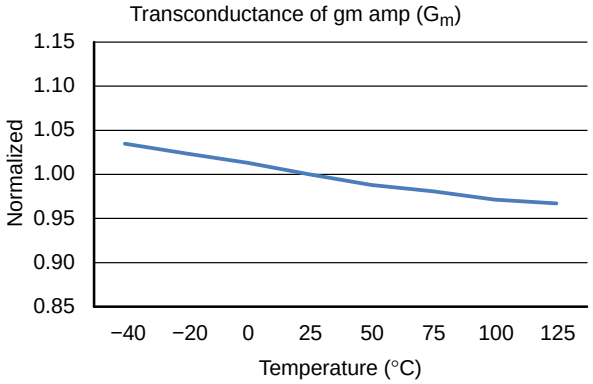

Figure 13. Transconductance of gm Amplifier vs. Temperature

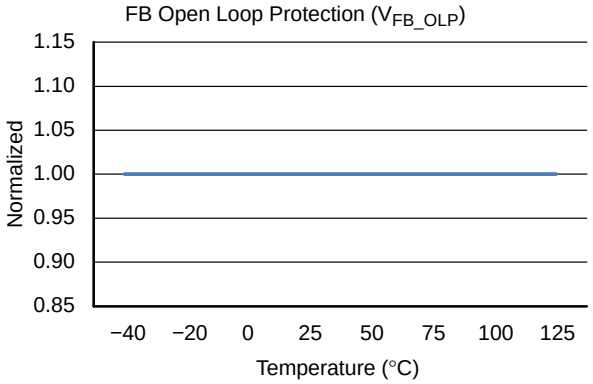

Figure 14. FB Open Loop Protection Voltage vs. Temperature

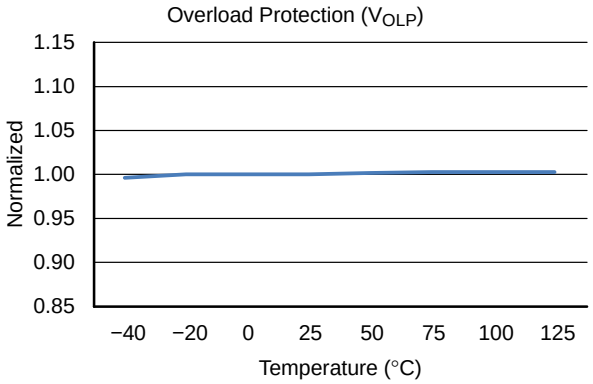

Figure 15. Overload Protection vs. Temperature

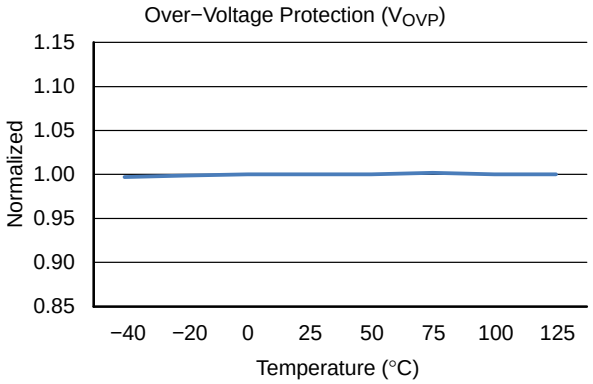

Figure 16. Over−Voltage Protection vs. Temperature

FUNCTIONAL DESCRIPTION

Startup and High−Voltage Regulator

During startup, an internal high−voltage current source (I_{CH}) of the high−voltage regulator supplies the internal bias current (I_{START}) and charges the external capacitor (C_A) connected to the V_{CC} pin, as illustrated in Figure 17. This internal high−voltage current source is enabled until V_{CC} reaches 10 V. During steady−state operation, this internal high−voltage regulator (HV_{REG}) maintains the V_{CC} with 10 V and provides operating current (I_{OP}) for all internal circuits. Therefore, FSL306LR needs no external bias circuit. The high−voltage regulator is disabled when the external bias is higher than 10 V.

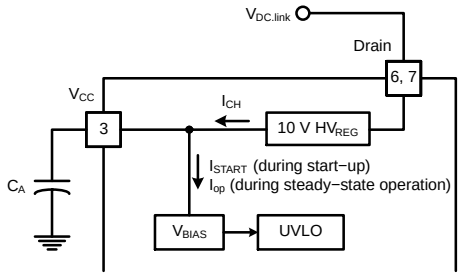

Figure 17. Startup and HV_{REG} Block

Oscillator Block

The oscillator frequency is set internally and the FSL306LR have random frequency fluctuation functions. Fluctuation of the switching frequency can reduce EMI by spreading the energy over a wider frequency range than the bandwidth measured by the EMI test equipment. The amount of EMI reduction is directly related to the range of the frequency variation. The range of frequency variation is fixed internally; however, its selection is randomly chosen by the combination of an external feedback voltage and an internal free−running oscillator. This randomly chosen switching frequency effectively spreads the EMI noise near switching frequency and allows the use of a cost−effective inductor instead of an AC input line filter to satisfy world−wide EMI requirements.

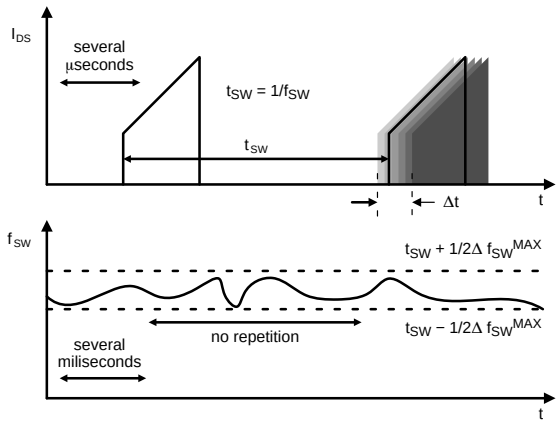

Figure 18. Frequency Fluctuation Waveform

Feedback Control

FSL306LR employs current−mode control with a transconductance amplifier for feedback control, as shown in Figure 19. Two resistors are typically used on the V_{FB} pin to sense output voltage. An external compensation circuit is recommended on the V_{COMP} pin to control output voltage. A built−in transconductance amplifier accurately controls output voltage without external components, such as Zener diode and transistor.

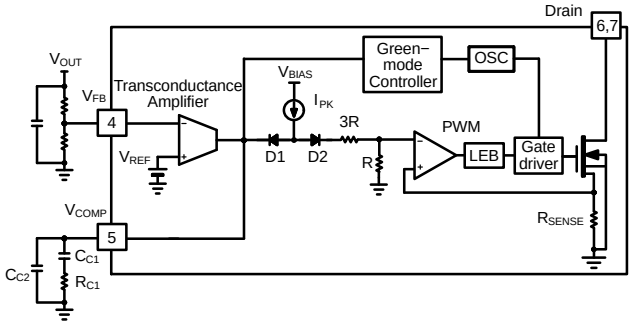

Figure 19. Pulse Width Modulation (PWM) Circuit

Transconductance Amplifier (gm Amplifier)

The output of the transconductance amplifier sources and sinks the current, respectively, to and from the compensation circuit connected on the V_{COMP} pin *(see Figure 20)*. This compensated V_{COMP} pin voltage controls the switching duty cycle by comparing with the voltage across the R_{SENSE}. When the feedback pin voltage exceeds the internal reference voltage (V_{REF}) of 2.5 V; the transconductance amplifier sinks the current from the compensation circuit, V_{COMP} is pulled down, and the duty cycle is reduced. This typically occurs when input voltage is increased or output load is decreased. A two−pole and one−zero compensation network is recommended for optimal output voltage control and AC dynamics. Typically 220 nF, 220 kΩ, and 330 pF are used for C_{C1}, R_{C1}, and C_{C2}, respectively.

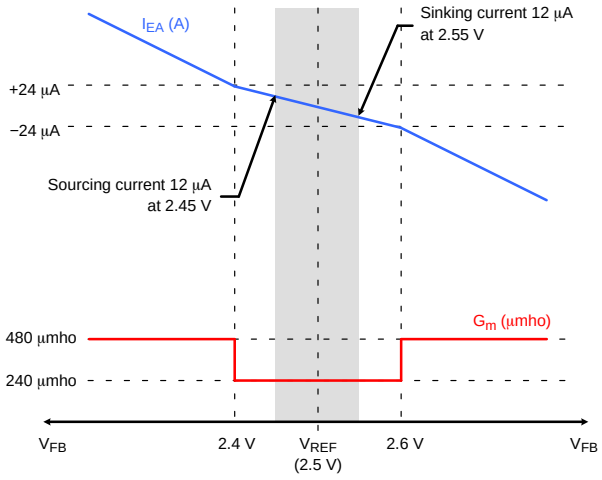

Figure 20. Characteristics of gm Amplifier

Pulse−by−pulse Current Limit

Because current−mode control is employed, the peak current flowing through the SENSEFET is limited by the inverting input of PWM comparator, as shown in Figure 19. Assuming that 50 μA current source flows only through the internal resistors (3R + R = 46 kΩ), the cathode voltage of diode D2 is about 2.4 V. Since D1 is blocked when V_{COMP} exceeds 2.4 V, the maximum voltage of the cathode of D2 is clamped at this voltage. Therefore, the peak value of the current of the SENSEFET is limited.

Leading Edge Blanking (LEB)

At the instant the internal SENSEFET is turned on; primary−side capacitance and secondary−side rectifier diode reverse recovery of flyback application, the freewheeling diode reverse recovery, and other parasitic capacitance of buck application typically cause a high−current spike through the SENSEFET. Excessive voltage across the sensing resistor (R_{SENSE}) leads to incorrect feedback operation in the current−mode control. To counter this effect, the FSL306LR have Leading−Edge Blanking (LEB) circuits *(see Figure 19)*. This circuit inhibits the PWM comparator for a short time (t_{LEB}) after the SENSEFET is turned on.

Protection Circuits

The protective functions include Overload Protection (OLP), Over−Voltage Protection (OVP), Under−Voltage Lockout (UVLO), Feedback Open Loop Protection (FB_OLP), Abnormal Over−Current Protection (AOCP), and Thermal Shutdown (TSD). All of the protections operate in Auto−Restart Mode. Since these protection circuits are fully integrated inside the IC without external components, reliability is improved without increasing cost and PCB space. If a fault condition occurs, switching is terminated and the SENSEFET remains off. At the same time, internal protection timing control is activated to decrease power consumption and stress on passive and active components during Auto−Restart. When internal protection timing control is activated, V_{CC} is regulated with 10 V through the internal high−voltage regulator until switching is terminated. This internal protection timing control continues until restart time (650 ms) is counted. After counting to 650 ms, the internal high−voltage regulator is disabled and V_{CC} is decreased. When V_{CC} reaches the UVLO stop voltage V_{STOP} (7 V), the protection is reset and the internal high−voltage current source charges the V_{CC} capacitor via the drain pin again. When V_{CC} reaches the UVLO start voltage, V_{START} (8 V), the FSL306LR resumes normal operation. In this manner, Auto−Restart can alternately enable and disable the switching of the power SENSEFET until the fault condition is eliminated.

Overload Protection (OLP)

Overload is defined as the load current exceeding a preset level due to an unexpected event. In this situation, the protection circuit should be activated to protect the SMPS. However, even when the SMPS operates normally, the OLP circuit can be enabled during the load transition or startup. To avoid this undesired operation, an internal fixed delay (40 ms) circuit determines whether it is a transient situation or a true overload situation *(see Figure 21)*. The current−mode feedback path limits the maximum power current and, when the output consumes more than this maximum power, the output voltage (V_O) decreases below its rated voltage. This reduces feedback pin voltage, which increases the output current of the internal transconductance amplifier. Eventually V_{COMP} is increased. When V_{COMP} reaches 3 V, the internal fixed OLP delay (40 ms) is activated. After this delay, the switching operation is terminated, as shown in Figure 22.

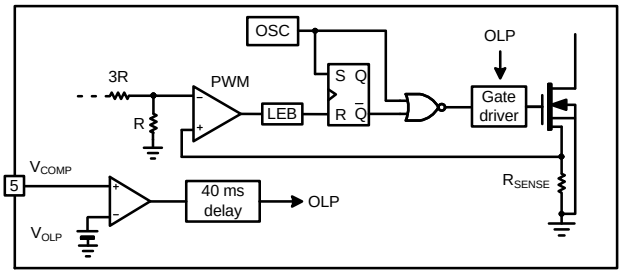

Figure 21. Overload Protection Internal Circuit

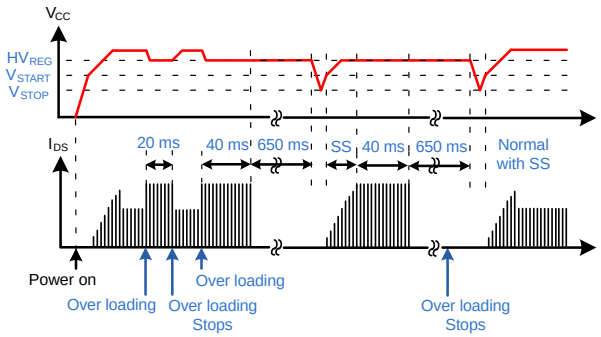

Figure 22. Overload Protection (OLP) Waveform

Abnormal Over−Current Protection (AOCP)

When output is shorted at high input voltage, much higher drain current peak than pulse−by−pulse current limit can flow through the SENSEFET because turn on time is the same as the minimum turn−on time of FSL306LR. Even OLP is occasionally not enough to protect the FSL306LR in that abnormal case, since severe current stress is imposed on the SENSEFET until OLP is triggered. FSL306LR includes the internal Abnormal Over−Current Protection (AOCP) circuit shown in Figure 23. The voltage across the R_{SENSE} is compared with a preset AOCP level (V_{AOCP}) after t_{LEB} and, if the voltage across the R_{SENSE} is greater than the AOCP level, the set signal is triggered after four switching times by an internal 2−bit counter, shutting down the SMPS, as shown in Figure 24. This LEB time can inhibit mis−triggering due to the leading−edge spike.

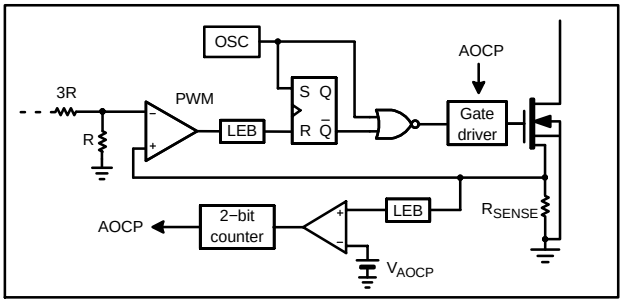

Figure 23. AOCP Circuit

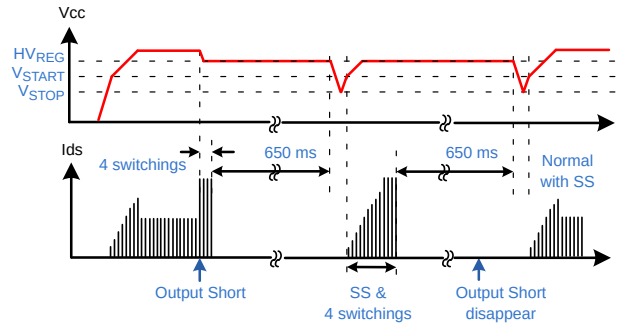

Figure 24. AOCP Waveform

Thermal Shutdown (TSD)

The SENSEFET and control IC integrated on the same package makes it easier to detect the temperature of the SENSEFET. When the junction temperature exceeds 135°C, thermal shutdown is activated. The FSL306LR are restarted after the temperature decreases to 60°C.

Over−Voltage Protection (OVP)

If any feedback loop components fail due to a soldering defect, V_{COMP} climbs up in manner similar to the overload situation, forcing the preset maximum current to be supplied to the SMPS until the OLP is triggered. In this case, excessive energy is provided to the output and the output voltage may exceed the rated voltage before the OLP is activated. To prevent this situation, an Over−Voltage Protection (OVP) circuit is employed. In general, output voltage can be monitored through V_{CC} and, when V_{CC} exceeds 24.5 V, OVP is triggered, resulting in termination of switching operation. To avoid undesired activation of OVP during normal operation, V_{CC} should be designed below 24.5 V *(see Figure 25)*.

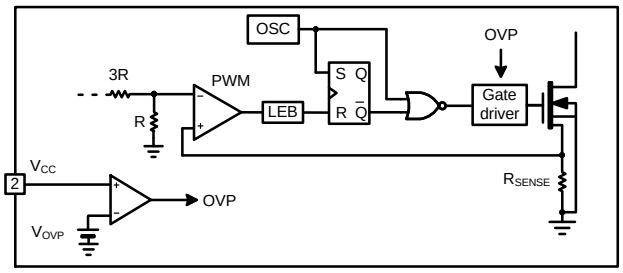

Figure 25. Over Voltage Protection Circuit

Feedback Open Loop Protection (FB_OLP)

In the event of a feedback loop failure, especially a shorted lower−side resistor of the feedback pin; not only does V_{COMP} rise in a similar manner to the overload situation, but V_{FB} starts to drop to IC ground level. Although OLP and OVP also can protect the SMPS in this situation, FB_OLP can reduce stress on SENSEFET more. If there is no FB_OLP, output voltage is much higher than rated voltage before OLP or OVP trigger. When V_{FB} drops below 0.5 V, FB_OLP is activated, switching off. To avoid undesired activation during startup, this function is disabled during soft−start time.

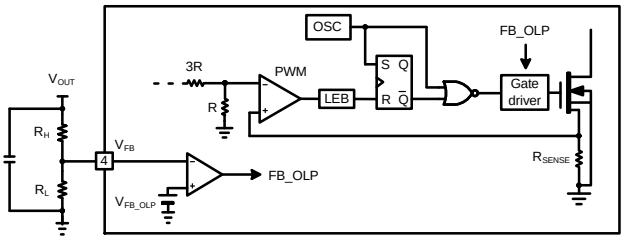

Figure 26. Feedback Open−loop Protection Circuit

Soft−Start

The internal soft−start circuit slowly increases the SENSEFET current after it starts. The typical soft−start time is 10 ms, as shown in Figure 27, where progressive increments of the SENSEFET current are allowed during startup. The pulse width to the power switching device is progressively increased to establish the correct working conditions for transformers, inductors, and capacitors. The voltage on the output capacitors is gradually increased to smoothly establish the required output voltage. Soft−start also helps to prevent transformer saturation and reduces stress on the secondary diode.

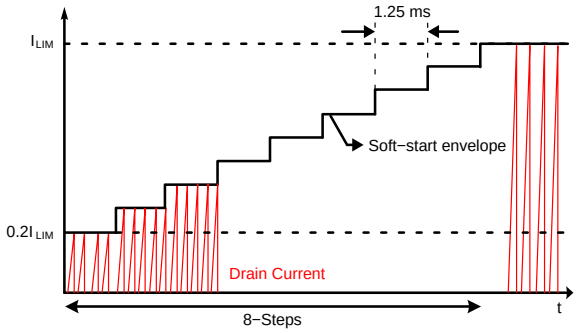

Figure 27. Internal Soft−Start

Burst Mode Operation

To minimize power dissipation in Standby Mode, the FSL306LR enters Burst Mode. As the load decreases, the comp voltage (V_{COMP}) decreases. As shown in Figure 28, the device automatically enters Burst Mode when the feedback voltage drops below V_{BURL}. At this point, switching stops and the output voltages start to drop at a rate dependent on the standby current load. This causes V_{COMP}

to rise. Once it passes V_{BURH}, switching resumes. V_{COMP} then falls and the process repeats. Burst Mode alternately enables and disables switching of the SENSEFET and reduces switching loss in Standby Mode.

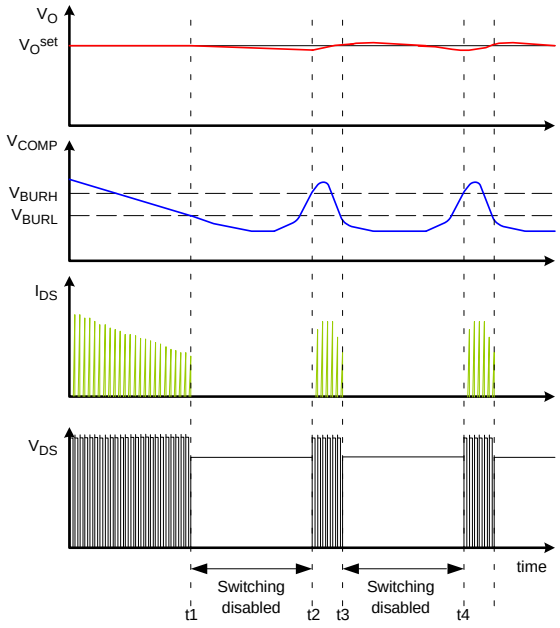

Figure 28. Burst Mode Operation

Green Mode Operation

As output load condition is reduced, the switching loss becomes the largest power loss factor. FSL306LR uses the V_{COMP} pin voltage to monitor output load condition. As output load decreases, V_{COMP} decreases and switching frequency declines, as shown in Figure 29. Once V_{COMP} falls to 0.8 V, the switching frequency varies between 21 kHz and 23 kHz before Burst Mode operation. At Burst Mode operation, random frequency fluctuation still functions.

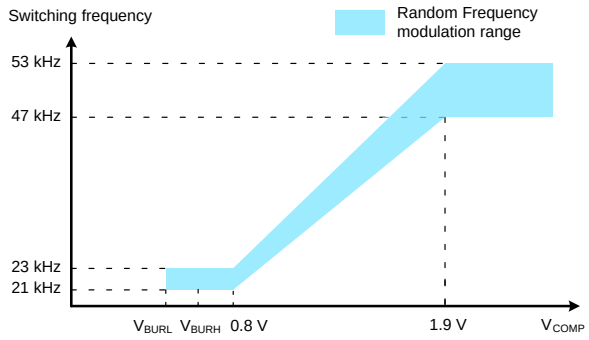

Figure 29. Green Mode Operation

Adjusting Current Limit

As shown in Figure 30, a combined 46 kΩ internal resistance (3R + R) is connected to the inverting lead on the PWM comparator. An external resistance of Rx on the I_{LIMIT} pin forms a parallel resistance with the 46 kΩ when the internal diodes are biased by the main current source of 50 μA. For example, FSL306LR have a typical SENSEFET peak current limit of 0.45 A. Current limit can be adjusted to 0.3 A by inserting R_X between the I_{LIMIT} pin and the ground. The value of the R_X can be estimated by the following equation:

$$0.45\ A : 0.3\ A = (46\ k\Omega + R_x) : R_x \qquad \text{(eq. 1)}$$

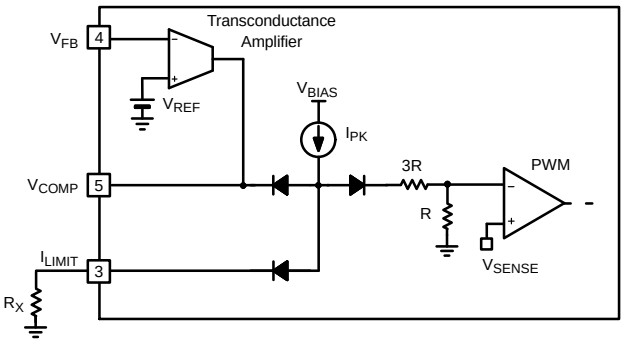

Figure 30. Current Limit Adjustment

TYPICAL APPLICATION CIRCUIT

Application	Input Voltage	Rated Output	Rated Power
Auxilary Power	85~300 VAC	12 V (150 mA)	2.05 W
Power Supply		5 V (50 mA)	

Key Design Notes

- Small current rating inductors (L1 & L2), an SMD−type resistor (R1), and an additional AC rectifying diode (D2) are placed for good EMI performance.
- External bias circuitry, a SMD−type resistor (R2), and a small−signal diode (D5) reduce power loss of the internal high−voltage regulator.

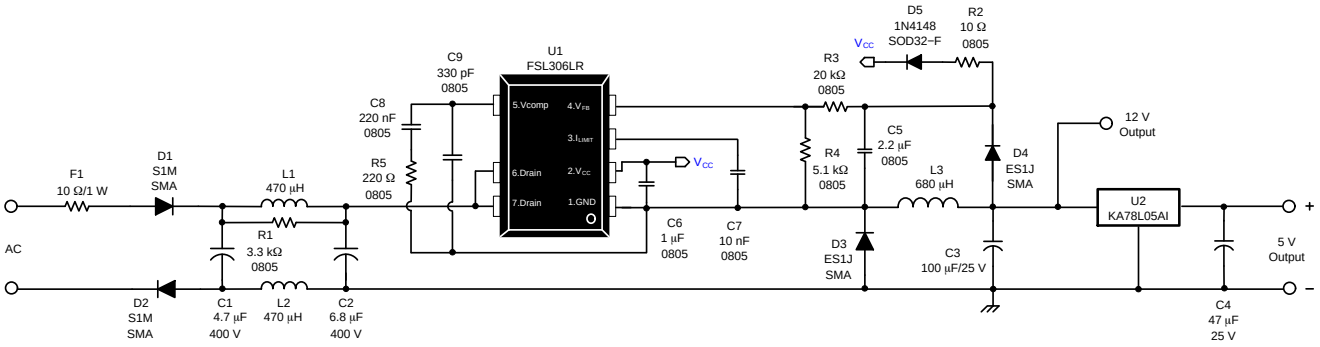

Figure 31. Schematic

Table 1. BILL OF MATERIALS

Part	Value	Note	Part	Value	Note
Fuse			**Diode**		
F1	10 W	1 W, Fusible Resistor	D1	S1M	1 A / 1000 V General−Purpose Rectifier
Resistor			D1	S1M	**onsemi**
R1	3.3 kΩ	SMD 0805, 5%	D2	S1M	1 A / 1000 V General−Purpose Rectifier
R2	10 Ω	SMD 0805, 5%			**onsemi**
R3	20 kΩ	SMD 0805, 1%	D3	ES1J	1 A / 600 V Ultra−Fast Recovery Rectifier
R4	5.1 kΩ	SMD 0805, 1%			**onsemi**
R5	220 kΩ	SMD 0805, 5%	D4	ES1J	1 A / 600 V Ultra−Fast Recovery Rectifier
Capacitor					**onsemi**
C1	4.7 μF / 400 V	Electrolytic	D5	1N4148	High Conductance Fast Diode
C2	6.8 μF / 400 V	Electrolytic			**onsemi**
C3	100 μF / 25 V	Electrolytic	**Inductor**		
C4	47 μF / 25 V	Electrolytic	L1	470 μH	SYNTON
C5	2.2 μF	SMD 0805	L2	470 μH	SYNTON
C6	1 μF	SMD 0805	L3	680 μH	PKS−0807−681K
C7	10 nF	SMD 0805			3L Electronic
C8	220 nF	SMD 0805			
C9	330 pF	SMD 0805	U1	FSL306LRN / FSL306LRL	**onsemi**
			U2	KA78L05AIMTF	0.1 A / 5 V Positive Voltage Regulator
					onsemi

ORDERING INFORMATION

Part Number	Operating Junction Temperature	PKG	Packing Method†	Typical Output Power (Note 8)			
				Current Limit	$R_{DS(ON),MAX}$	85 V_{AC}~265 V_{AC} & Open Frame (Note 9)	
						Buck Application (Note 10)	Flyback Application
FSL306LRN	−40°C~125°C	7−DIP	Rail	0.45 A	184 Ω	3 W	7 W
FSL306LRLX		7−LSOP	Tape & Reel				

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

8. The junction temperature can limit the maximum output power.
9. Maximum practical continuous power in an open−frame design at 50°C ambient.
10. Based on 15 V output voltage condition. Output voltage can limit the maximum output power.

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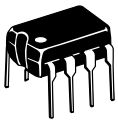

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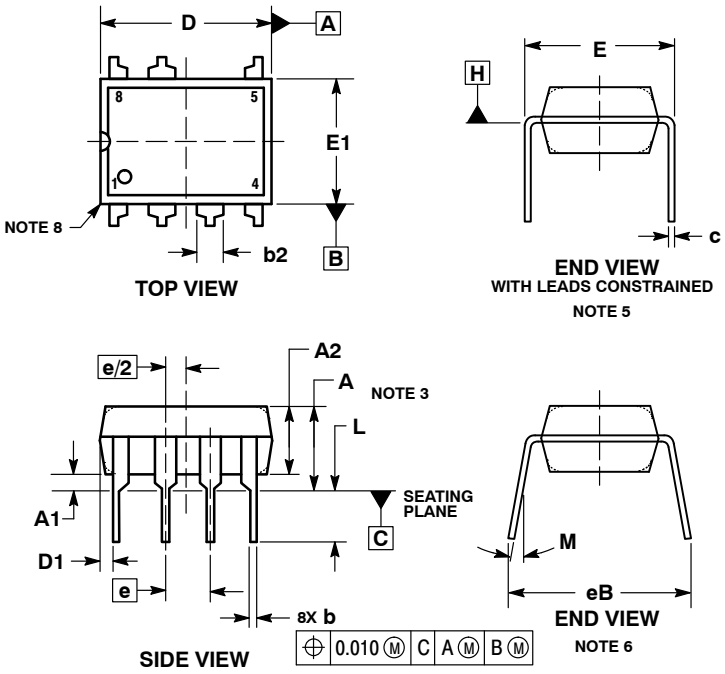

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2. CONTROLLING DIMENSION: INCHES.
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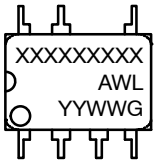
4. DIMENSIONS D, D1 AND E1 DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS. MOLD FLASH OR PROTRUSIONS ARE NOT TO EXCEED 0.10 INCH.
5. DIMENSION E IS MEASURED AT A POINT 0.015 BELOW DATUM PLANE H WITH THE LEADS CONSTRAINED PERPENDICULAR TO DATUM C.
6. DIMENSION eB IS MEASURED AT THE LEAD TIPS WITH THE LEADS UNCONSTRAINED.
7. DATUM PLANE H IS COINCIDENT WITH THE BOTTOM OF THE LEADS, WHERE THE LEADS EXIT THE BODY.
8. PACKAGE CONTOUR IS OPTIONAL (ROUNDED OR SQUARE CORNERS).

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	----	0.210	---	5.33
A1	0.015	----	0.38	---
A2	0.115	0.195	2.92	4.95
b	0.014	0.022	0.35	0.56
b2	0.060 TYP		1.52 TYP	
C	0.008	0.014	0.20	0.36
D	0.355	0.400	9.02	10.16
D1	0.005	----	0.13	---
E	0.300	0.325	7.62	8.26
E1	0.240	0.280	6.10	7.11
e	0.100 BSC		2.54 BSC	
eB	----	0.430	---	10.92
L	0.115	0.150	2.92	3.81
M	----	10°	---	10°

GENERIC MARKING DIAGRAM*



XXXX	= Specific Device Code
A	= Assembly Location
WL	= Wafer Lot
YY	= Year
WW	= Work Week
G	= Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

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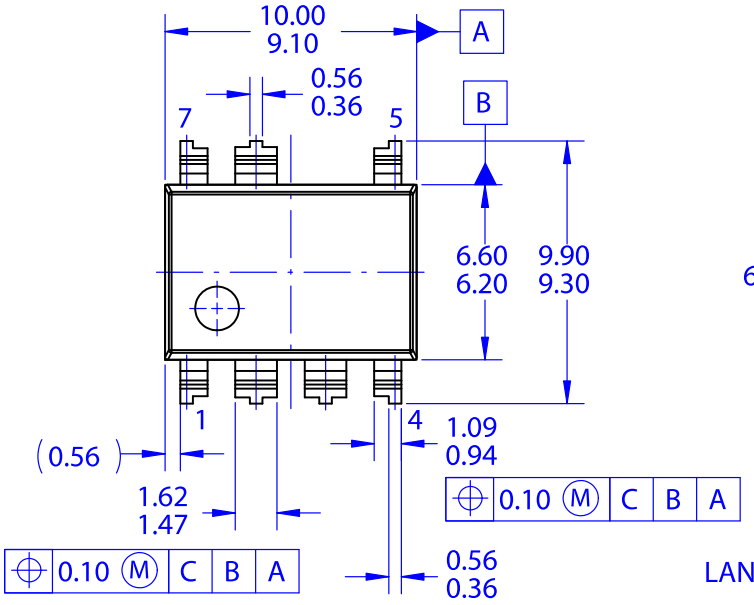

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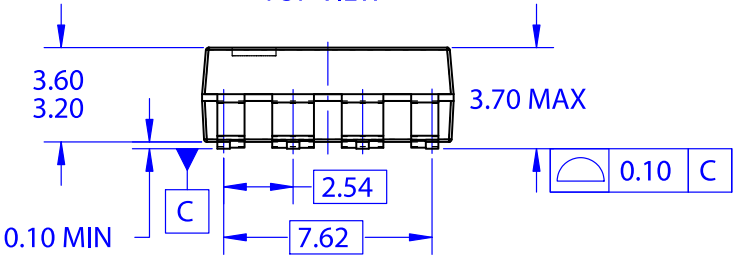

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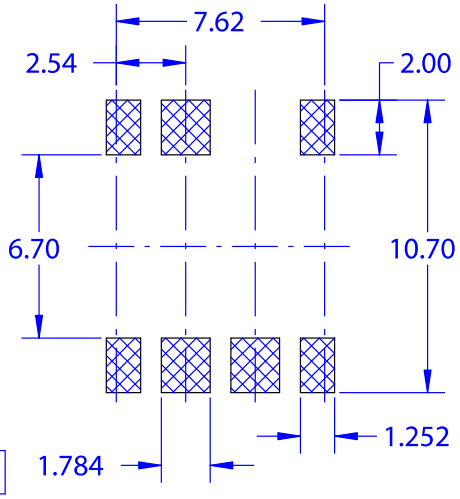

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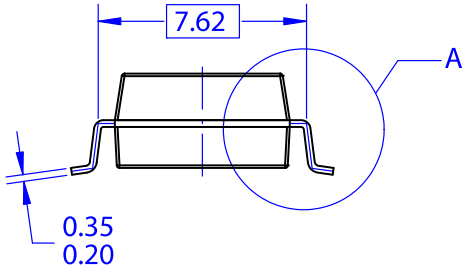

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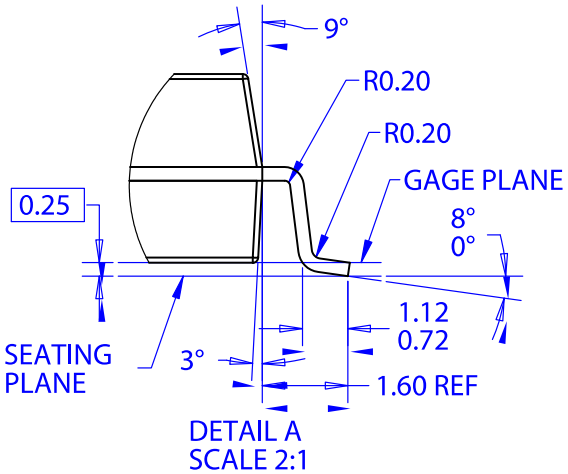

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